

## General Description

The WSR3090 is the highest performance trench N-ch MOSFET with extreme high cell density , which provide excellent RDSON and gate charge for most of the synchronous buck converter applications .

The WSR3090 meet the RoHS and Green Product requirement , 100% EAS guaranteed with full function reliability approved.

## Features

- Advanced high cell density Trench technology
- Super Low Gate Charge
- Excellent CdV/dt effect decline
- 100% EAS Guaranteed
- Green Device Available

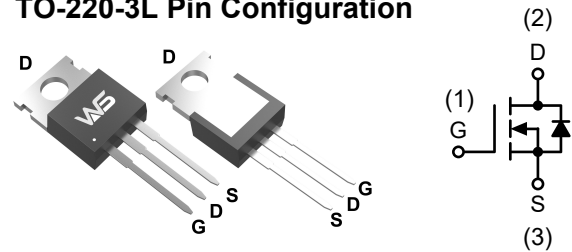
## Product Summary

| $BV_{DSS}$ | $R_{DSON}$ | $I_D$ |
|------------|------------|-------|
| 30V        | 4.5mΩ      | 90A   |

## Applications

- High Frequency Point-of-Load Synchronous Buck Converter for MB/NB/UMPC/VGA
- Networking DC-DC Power System
- Load Switch

## TO-220-3L Pin Configuration



## Absolute Maximum Ratings

| Symbol                | Parameter                                  | Rating     |              | Units      |
|-----------------------|--------------------------------------------|------------|--------------|------------|
|                       |                                            | 10s        | Steady State |            |
| $V_{DS}$              | Drain-Source Voltage                       | 30         |              | V          |
| $V_{GS}$              | Gate-Source Voltage                        | $\pm 20$   |              | V          |
| $I_D@T_C=25^\circ C$  | Continuous Drain Current, $V_{GS} @ 10V^1$ | 90         |              | A          |
| $I_D@T_C=100^\circ C$ | Continuous Drain Current, $V_{GS} @ 10V^1$ | 60         |              | A          |
| $I_D@T_A=25^\circ C$  | Continuous Drain Current, $V_{GS} @ 10V^1$ | 27         | 17           | A          |
| $I_D@T_A=70^\circ C$  | Continuous Drain Current, $V_{GS} @ 10V^1$ | 23         | 14.5         | A          |
| $I_{DM}$              | Pulsed Drain Current <sup>2</sup>          | 160        |              | A          |
| EAS                   | Single Pulse Avalanche Energy <sup>3</sup> | 252        |              | mJ         |
| $I_{AS}$              | Avalanche Current                          | 48         |              | A          |
| $P_D@T_C=25^\circ C$  | Total Power Dissipation <sup>4</sup>       | 53         |              | W          |
| $P_D@T_A=25^\circ C$  | Total Power Dissipation <sup>4</sup>       | 6          | 2.0          | W          |
| $T_{STG}$             | Storage Temperature Range                  | -55 to 175 |              | $^\circ C$ |
| $T_J$                 | Operating Junction Temperature Range       | -55 to 175 |              | $^\circ C$ |

## Thermal Data

| Symbol          | Parameter                                                       | Typ. | Max. | Unit         |
|-----------------|-----------------------------------------------------------------|------|------|--------------|
| $R_{\theta JA}$ | Thermal Resistance Junction-ambient (Steady State) <sup>1</sup> | ---  | 62   | $^\circ C/W$ |
| $R_{\theta JA}$ | Thermal Resistance Junction-Ambient <sup>1</sup> (t ≤ 10s)      | ---  | 25   | $^\circ C/W$ |
| $R_{\theta JC}$ | Thermal Resistance Junction-Case <sup>1</sup>                   | ---  | 2.8  | $^\circ C/W$ |

**Electrical Characteristics (T<sub>J</sub>=25 °C, unless otherwise noted)**

| Symbol                              | Parameter                                      | Conditions                                                                              | Min. | Typ.  | Max. | Unit  |
|-------------------------------------|------------------------------------------------|-----------------------------------------------------------------------------------------|------|-------|------|-------|
| BV <sub>DSS</sub>                   | Drain-Source Breakdown Voltage                 | V <sub>GS</sub> =0V, I <sub>D</sub> =250uA                                              | 30   | ---   | ---  | V     |
| ΔBV <sub>DSS</sub> /ΔT <sub>J</sub> | BVDSS Temperature Coefficient                  | Reference to 25°C, I <sub>D</sub> =1mA                                                  | ---  | 0.028 | ---  | V/°C  |
| R <sub>DS(ON)</sub>                 | Static Drain-Source On-Resistance <sup>2</sup> | V <sub>GS</sub> =10V, I <sub>D</sub> =30A                                               | ---  | 4.5   | 5.5  | mΩ    |
|                                     |                                                | V <sub>GS</sub> =4.5V, I <sub>D</sub> =15A                                              | ---  | 7.8   | 9    |       |
| V <sub>GS(th)</sub>                 | Gate Threshold Voltage                         | V <sub>GS</sub> =V <sub>DS</sub> , I <sub>D</sub> =250uA                                | 1.0  | 1.5   | 2.5  | V     |
| ΔV <sub>GS(th)</sub>                | V <sub>GS(th)</sub> Temperature Coefficient    |                                                                                         | ---  | -6.16 | ---  | mV/°C |
| I <sub>DSS</sub>                    | Drain-Source Leakage Current                   | V <sub>DS</sub> =24V, V <sub>GS</sub> =0V, T <sub>J</sub> =25°C                         | ---  | ---   | 1    | uA    |
|                                     |                                                | V <sub>DS</sub> =24V, V <sub>GS</sub> =0V, T <sub>J</sub> =55°C                         | ---  | ---   | 5    |       |
| I <sub>GSS</sub>                    | Gate-Source Leakage Current                    | V <sub>GS</sub> =±20V, V <sub>DS</sub> =0V                                              | ---  | ---   | ±100 | nA    |
| g <sub>fs</sub>                     | Forward Transconductance                       | V <sub>DS</sub> =5V, I <sub>D</sub> =30A                                                | ---  | 43    | ---  | S     |
| R <sub>g</sub>                      | Gate Resistance                                | V <sub>DS</sub> =0V, V <sub>GS</sub> =0V, f=1MHz                                        | ---  | 1.7   | 3.1  | Ω     |
| Q <sub>g</sub>                      | Total Gate Charge (4.5V)                       | V <sub>DS</sub> =15V, V <sub>GS</sub> =4.5V, I <sub>D</sub> =15A                        | ---  | 20    | 28   | nC    |
| Q <sub>gs</sub>                     | Gate-Source Charge                             |                                                                                         | ---  | 7.6   | 10.6 |       |
| Q <sub>gd</sub>                     | Gate-Drain Charge                              |                                                                                         | ---  | 7.2   | 10.1 |       |
| T <sub>d(on)</sub>                  | Turn-On Delay Time                             | V <sub>DD</sub> =15V, V <sub>GS</sub> =10V, R <sub>G</sub> =3.3Ω<br>I <sub>D</sub> =15A | ---  | 11    | 15.6 | ns    |
| T <sub>r</sub>                      | Rise Time                                      |                                                                                         | ---  | 15    | 27   |       |
| T <sub>d(off)</sub>                 | Turn-Off Delay Time                            |                                                                                         | ---  | 10.6  | 21.2 |       |
| T <sub>f</sub>                      | Fall Time                                      |                                                                                         | ---  | 37.3  | 74.6 |       |
| C <sub>iss</sub>                    | Input Capacitance                              | V <sub>DS</sub> =15V, V <sub>GS</sub> =0V, f=1MHz                                       | ---  | 2295  | 3213 | pF    |
| C <sub>oss</sub>                    | Output Capacitance                             |                                                                                         | ---  | 570   | 374  |       |
| C <sub>rss</sub>                    | Reverse Transfer Capacitance                   |                                                                                         | ---  | 210   | 294  |       |

**Guaranteed Avalanche Characteristics**

| Symbol | Parameter                                  | Conditions                                          | Min. | Typ. | Max. | Unit |
|--------|--------------------------------------------|-----------------------------------------------------|------|------|------|------|
| EAS    | Single Pulse Avalanche Energy <sup>5</sup> | V <sub>DD</sub> =25V, L=0.1mH, I <sub>AS</sub> =24A | 63   | ---  | ---  | mJ   |

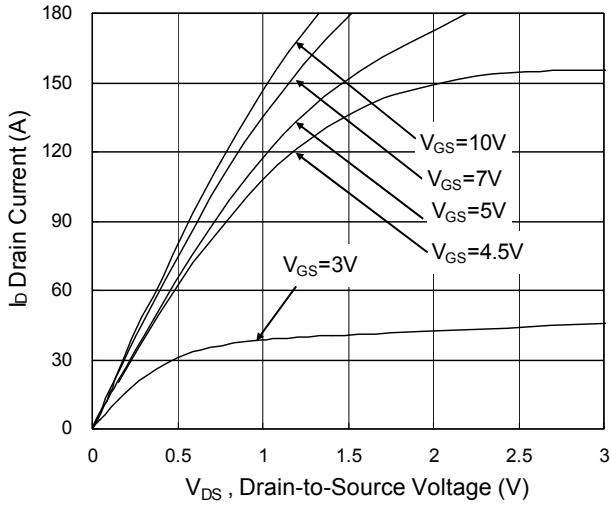
**Diode Characteristics**

| Symbol          | Parameter                                | Conditions                                                    | Min. | Typ. | Max. | Unit |
|-----------------|------------------------------------------|---------------------------------------------------------------|------|------|------|------|
| I <sub>S</sub>  | Continuous Source Current <sup>1,6</sup> | V <sub>G</sub> =V <sub>D</sub> =0V, Force Current             | ---  | ---  | 35   | A    |
| I <sub>SM</sub> | Pulsed Source Current <sup>2,6</sup>     |                                                               | ---  | ---  | 160  | A    |
| V <sub>SD</sub> | Diode Forward Voltage <sup>2</sup>       | V <sub>GS</sub> =0V, I <sub>S</sub> =1A, T <sub>J</sub> =25°C | ---  | ---  | 1    | V    |
| t <sub>rr</sub> | Reverse Recovery Time                    | IF=30A, dI/dt=100A/μs, T <sub>J</sub> =25°C                   | ---  | 30   | ---  | nS   |
| Q <sub>rr</sub> | Reverse Recovery Charge                  |                                                               | ---  | 24   | ---  | nC   |

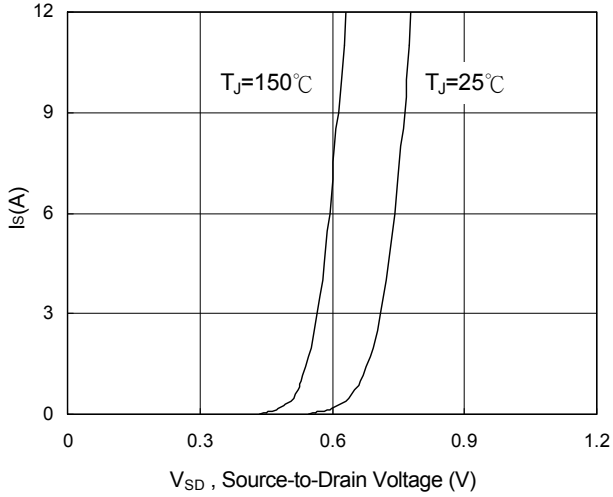
Note :

- The data tested by surface mounted on a 1 inch<sup>2</sup> FR-4 board with 20Z copper, t<10sec.
- The data tested by pulsed, pulse width ≤ 300us, duty cycle ≤ 2%
- The EAS data shows Max. rating. The test condition is V<sub>DD</sub>=25V, V<sub>GS</sub>=10V, L=0.1mH, I<sub>AS</sub>=24A
- The power dissipation is limited by 175°C junction temperature
- The Min. value is 100% EAS tested guarantee.
- The data is theoretically the same as I<sub>D</sub> and I<sub>DM</sub>, in real applications, should be limited by total power dissipation.

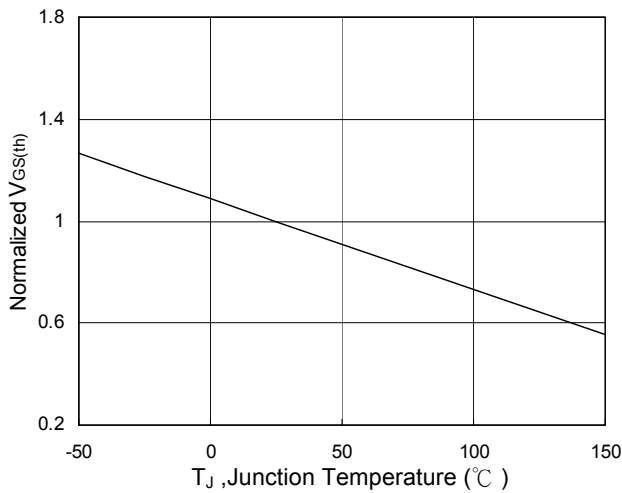
**Typical Characteristics**



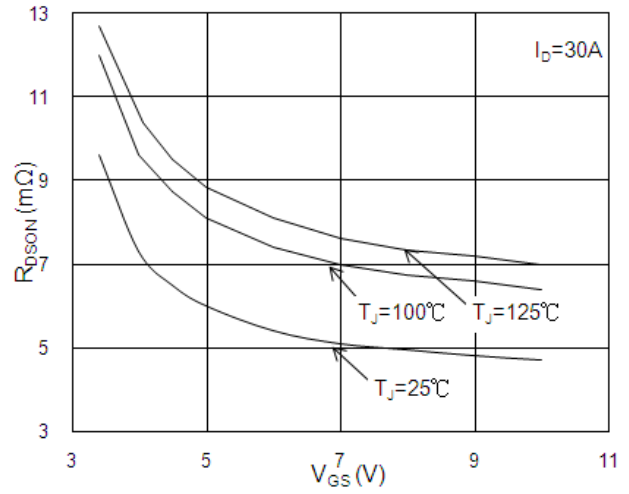
**Fig.1 Typical Output Characteristics**



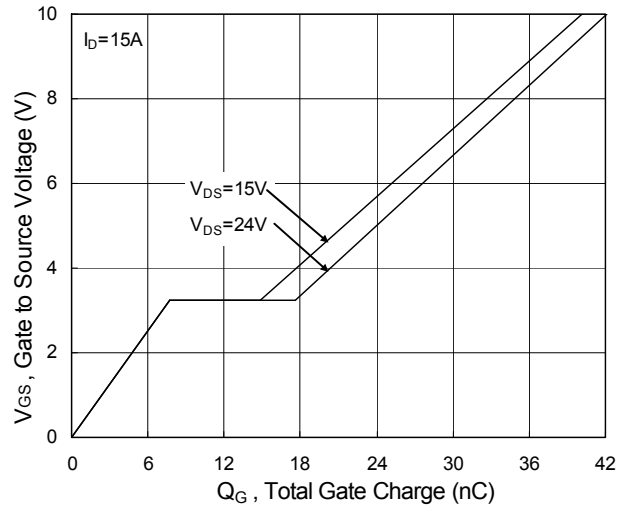
**Fig.3 Forward Characteristics of Reverse**



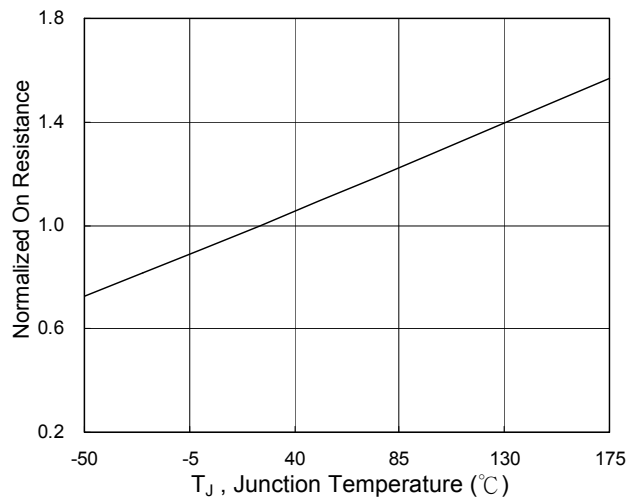
**Fig.5 Normalized  $V_{GS(th)}$  vs.  $T_J$**



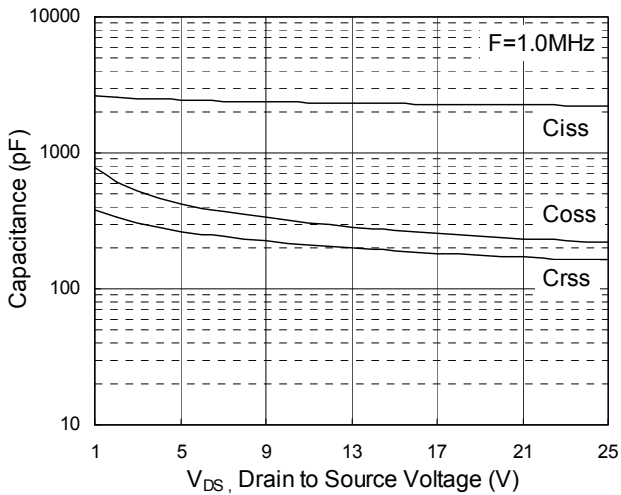
**Fig.2 On-Resistance vs. G-S Voltage**



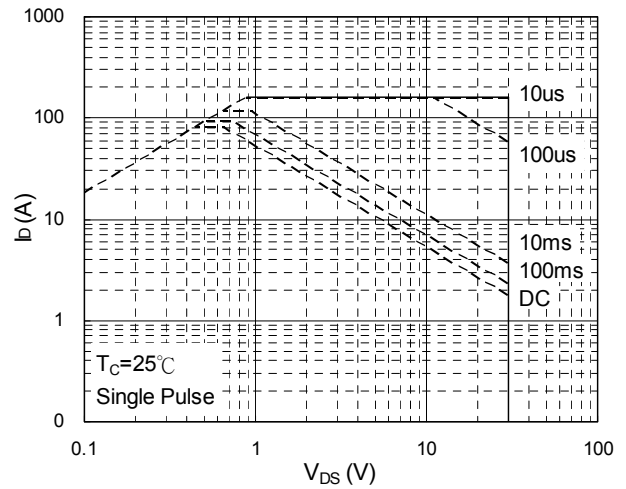
**Fig.4 Gate-Charge Characteristics**



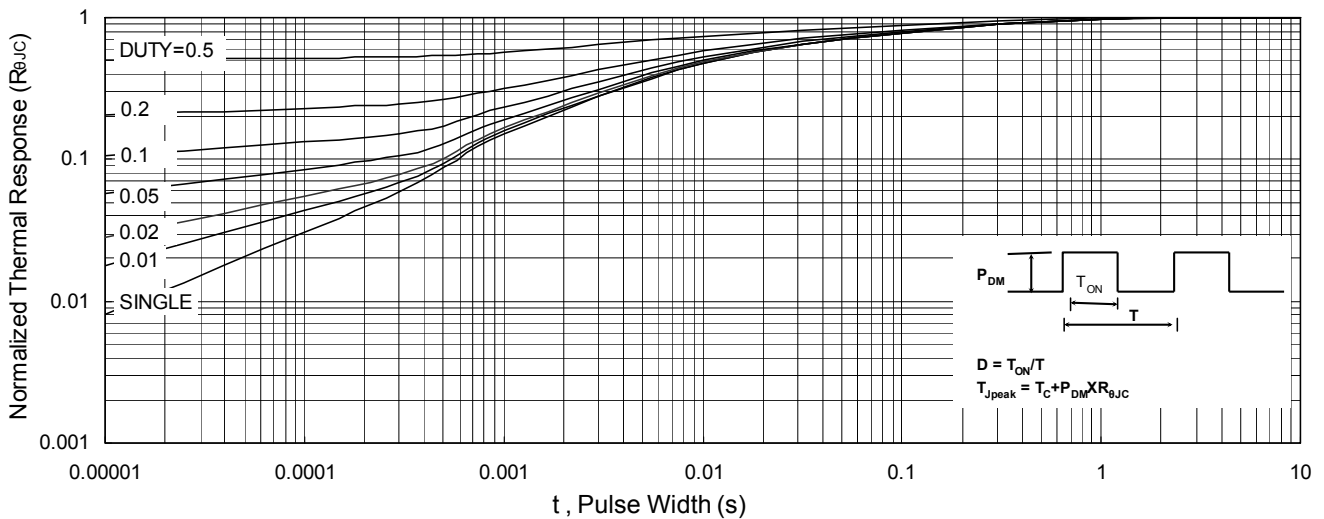
**Fig.6 Normalized  $R_{DS(on)}$  vs.  $T_J$**



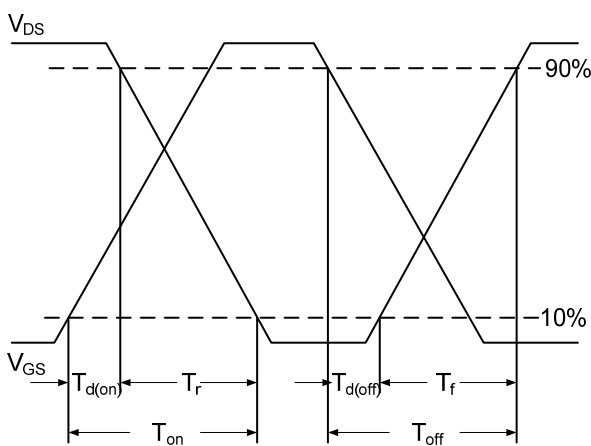
**Fig.7 Capacitance**



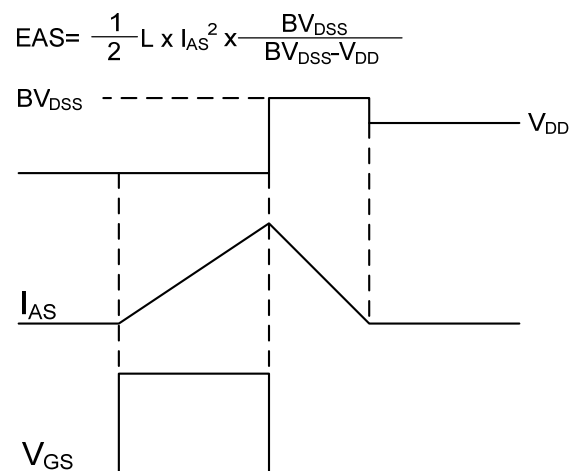
**Fig.8 Safe Operating Area**



**Fig.9 Normalized Maximum Transient Thermal Impedance**

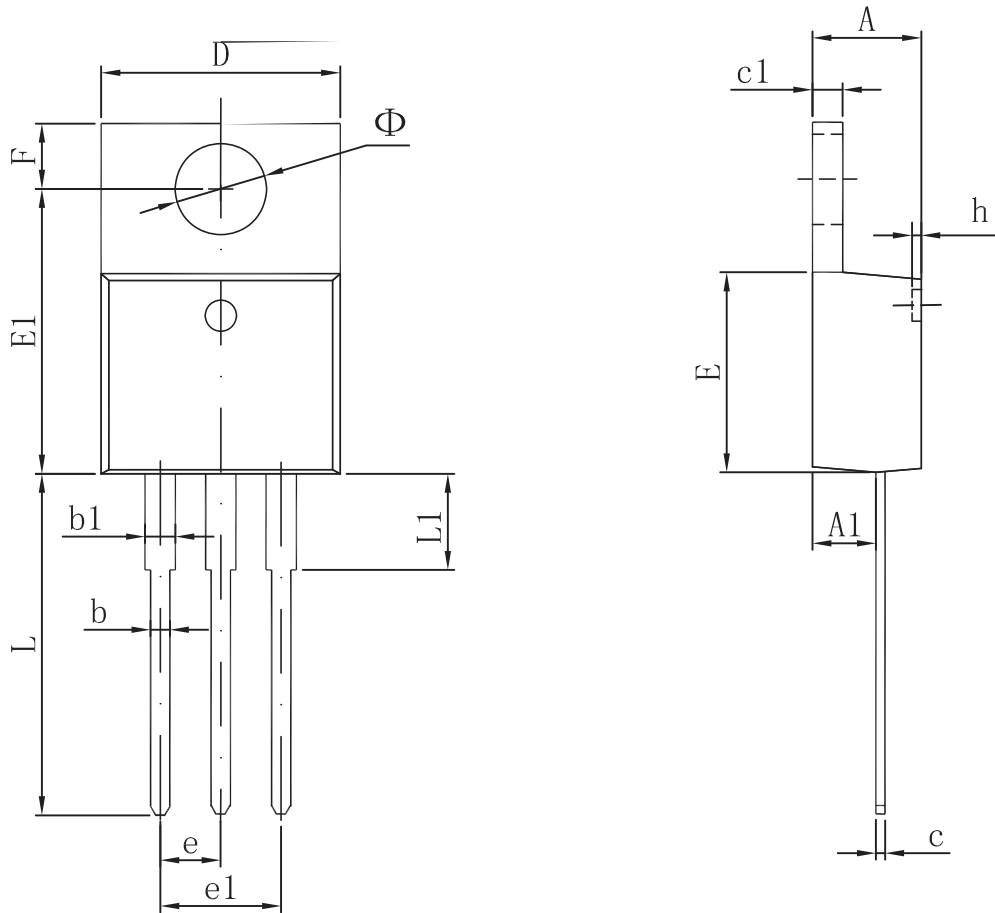


**Fig.10 Switching Time Waveform**



**Fig.11 Unclamped Inductive Switching Waveform**

**Packaging information**



| Symbol | Dimensions In Millimeters |        | Dimensions In Inches |       |
|--------|---------------------------|--------|----------------------|-------|
|        | Min                       | Max    | Min                  | Max   |
| A      | 4.470                     | 4.670  | 0.176                | 0.184 |
| A1     | 2.520                     | 2.820  | 0.099                | 0.111 |
| b      | 0.710                     | 0.910  | 0.028                | 0.036 |
| b1     | 1.170                     | 1.370  | 0.046                | 0.054 |
| c      | 0.310                     | 0.530  | 0.012                | 0.021 |
| c1     | 1.170                     | 1.370  | 0.046                | 0.054 |
| D      | 10.010                    | 10.310 | 0.394                | 0.406 |
| E      | 8.500                     | 8.900  | 0.335                | 0.350 |
| E1     | 12.060                    | 12.460 | 0.475                | 0.491 |
| e      | 2.540 TYP                 |        | 0.100 TYP            |       |
| e1     | 4.980                     | 5.180  | 0.196                | 0.204 |
| F      | 2.590                     | 2.890  | 0.102                | 0.114 |
| h      | 0.000                     | 0.300  | 0.000                | 0.012 |
| L      | 13.400                    | 13.800 | 0.528                | 0.543 |
| L1     | 3.560                     | 3.960  | 0.140                | 0.156 |
| $\Phi$ | 3.735                     | 3.935  | 0.147                | 0.155 |



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